

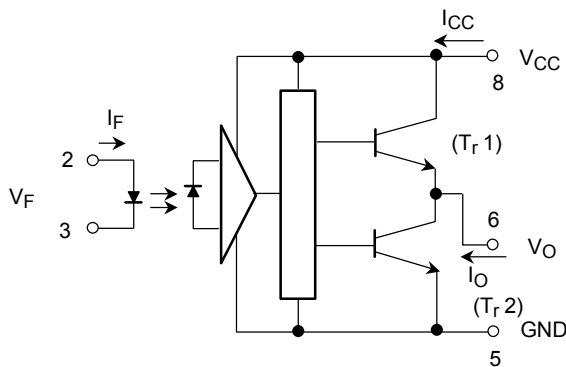
# TLP251

- Inverter For Air Conditionor
- Induction Heating
- Transistor Inverter
- Power MOS FET Gate Drive
- IGBT Gate Drive

The TOSHIBA TLP251 consists of a GaAlAs light emitting diode and a integrated photodetector.  
 This unit is 8-lead DIP package.  
 TLP251 is suitable for gate driving circuit of IGBT or power MOS FET.  
 Especially TLP251 is capable of "direct" gate drive of lower power IGBTs.  
 (~15A)

- Input threshold current:  $I_F=5\text{mA}(\text{max.})$
- Supply current ( $I_{CC}$ ):  $11\text{mA}(\text{max.})$
- Supply voltage ( $V_{CC}$ ):  $10\text{--}35\text{V}$
- Output current ( $I_O$ ):  $\pm 0.4\text{A}(\text{max.})$
- Switching time ( $t_{pLH} / t_{pHL}$ ):  $1\mu\text{s}(\text{max.})$
- Isolation voltage:  $2500\text{Vrms}(\text{min.})$
- UL recognized: UL1577, file no.E67349

### Schematic

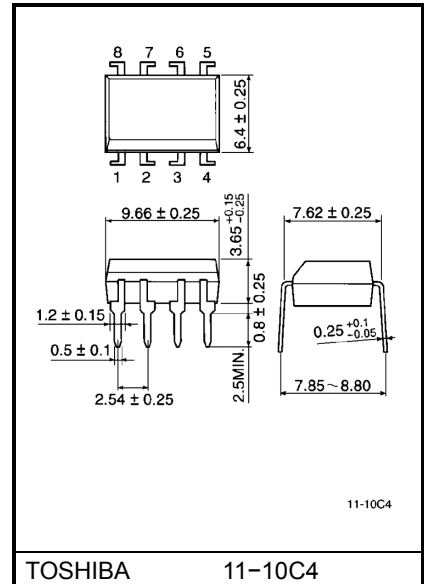


A  $0.1\mu\text{F}$  bypass capacitor must be connected between pin 8 and 5(see Note 5).

### Truth Table

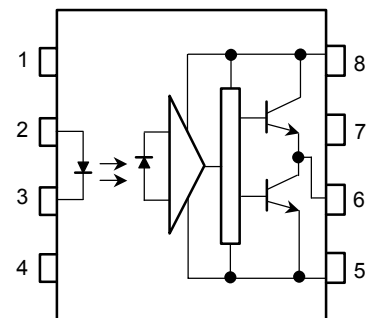
		Tr1	Tr2
Input LED	On	On	Off
	Off	Off	On

Unit in mm



Weight: 0.54g

### Pin Configuration (top view)



- 1 : N.C.
- 2 : Anode
- 3 : Cathode
- 4 : N.C.
- 5 : Gnd
- 6 :  $V_O$  (Output)
- 7 : N.C.
- 8 :  $V_{CC}$

## Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
LED	Forward current	$I_F$	20	mA	
	Forward current derating (Ta ≥ 70°C)	$\Delta I_F / \Delta T_a$	- 0.36	mA / °C	
	Peak transient forward current (Note 1)	$I_{FPT}$	1	A	
	Reverse voltage	$V_R$	5	V	
	Junction temperature	$T_j$	125	°C	
Detector	"H" peak output current ( $P_W \leq 2.0\mu s, f \leq 15kHz$ ) (Note 2)	$I_{OPH}$	- 0.4	A	
	"L" peak output current ( $P_W \leq 2.0\mu s, f \leq 15kHz$ ) (Note 2)	$I_{OPL}$	0.4	A	
	Output voltage	(Ta ≤ 70°C)	$V_O$	35	V
		(Ta = 85°C)		24	
	Supply voltage	(Ta ≤ 70°C)	$V_{CC}$	35	V
		(Ta = 85°C)		24	
	Output voltage derating (Ta ≥ 70°C)		$\Delta V_O / \Delta T_a$	- 0.73	V / °C
	Supply voltage derating (Ta ≥ 70°C)		$\Delta V_{CC} / \Delta T_a$	- 0.73	V / °C
	Junction temperature		$T_j$	125	°C
	Operating frequency (Note 3)		f	25	kHz
Operating temperature range		$T_{opr}$	-20~85	°C	
Storage temperature range		$T_{stg}$	-55~125	°C	
Lead soldering temperature(10s)		$T_{sol}$	260	°C	
Isolation voltage (AC, 1min., R.H.≤ 60%) (Note 4)		$BV_S$	2500	Vrms	

(Note 1) Pulse width  $P_W \leq 1\mu s, 300pps$

(Note 2) Exponential waveform

(Note 3) Exponential waveform,  $I_{OPH} \leq -0.25A(\leq 2.0\mu s), I_{OPL} \leq +0.25A(\leq 2.0\mu s)$

(Note 4) Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

(Note 5) A ceramic capacitor(0.1μF)should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property.The total lead length between capacitor and coupler should not exceed 1cm.

## Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Input current, on	$I_{F(ON)}$	7	8	10	mA
Input voltage, off	$V_{F(OFF)}$	0	—	0.8	V
Supply voltage	$V_{CC}$	10	—	30   20	V
Peak output current	$I_{OPH} / I_{OPL}$	—	—	±0.1	A
Operating temperature	$T_{opr}$	-20	25	70   85	°C

## Electrical Characteristics (Ta = -20~70°C, unless otherwise specified)

Characteristic		Symbol	Test Circuit	Test Condition	Min.	Typ.*	Max.	Unit	
Input forward voltage		$V_F$	—	$I_F = 10 \text{ mA}$ , $T_a = 25^\circ\text{C}$	—	1.6	1.8	V	
Temperature coefficient of forward voltage		$\Delta V_F / \Delta T_a$	—	$I_F = 10 \text{ mA}$	—	-2.0	—	mV / °C	
Input reverse current		$I_R$	—	$V_R = 5\text{V}$ , $T_a = 25^\circ\text{C}$	—	—	10	μA	
Input capacitance		$C_T$	—	$V = 0$ , $f = 1\text{MHz}$ , $T_a = 25^\circ\text{C}$	—	45	250	pF	
Output current	“H” level	$I_{OPH}$	3	$V_{CC}=30\text{V}$ (*1)	$I_F = 10\text{mA}$ $V_{8-6} = 4\text{V}$	-0.1	-0.25	—	A
	“L” level	$I_{OPL}$	2		$I_F = 0$ $V_{6-5} = 2.5\text{V}$	0.1	0.2	—	
Output voltage	“H” level	$V_{OH}$	4	$V_{CC1} = +15\text{V}$ , $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$ , $I_F = 5\text{mA}$	11	13.2	—	V	
	“L” level	$V_{OL}$	5		$V_{CC1} = +15\text{V}$ , $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$ , $V_F = 0.8\text{V}$	—	-14.5		-12.5
Supply current	“H” level	$I_{CCH}$	—	$V_{CC} = 30\text{V}$ , $I_F = 10\text{mA}$ $T_a = 25^\circ\text{C}$	—	7.5	—	mA	
					—	—	11		
	“L” level	$I_{CCL}$	—		$V_{CC} = 30\text{V}$ , $I_F = 0\text{mA}$ $T_a = 25^\circ\text{C}$	—	8		—
						—	—		11
Threshold input current	“Output L → H”	$I_{FLH}$	—	$V_{CC1} = +15\text{V}$ , $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$ , $V_O > 0\text{V}$	—	1.2	5	mA	
Threshold input voltage	“Output H → L”	$V_{FLH}$	—	$V_{CC1} = +15\text{V}$ , $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$ , $V_O < 0\text{V}$	0.8	—	—	V	
Supply voltage		$V_{CC}$	—		10	—	35	V	
Capacitance (input-output)		$C_s$	—	$V_s = 0$ , $f = 1\text{MHz}$ $T_a = 25^\circ\text{C}$	—	1.0	2.0	pF	
Resistance (input-output)		$R_s$	—	$V_s = 500\text{V}$ , $T_a = 25^\circ\text{C}$ $R.H. \leq 60\%$	$1 \times 10^{12}$	$10^{14}$	—	Ω	

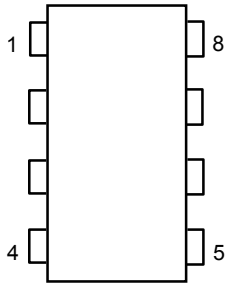
\* All typical values are at  $T_a=25^\circ\text{C}$  (\*1): Duration of  $I_O$  time  $\leq 50\mu\text{s}$

## Switching Characteristics (Ta = -20~70°C, unless otherwise specified)

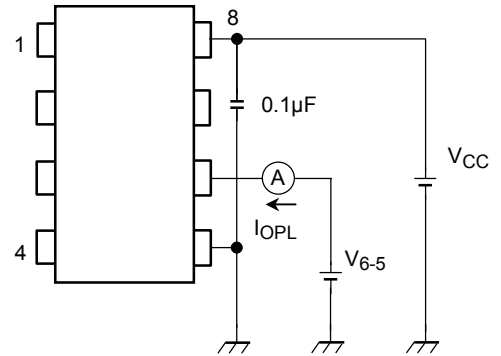
Characteristic		Symbol	Test Cir-cuit	Test Condition	Min.	Typ.*	Max.	Unit
Propagation delay time	L→H	t <sub>pLH</sub>	6	I <sub>F</sub> = 8mA V <sub>CC1</sub> = +15V, V <sub>EE1</sub> = -15V R <sub>L</sub> = 200 Ω	—	0.25	1.0	μs
	H→L	t <sub>pHL</sub>			—	0.25	1.0	
Output rise time		t <sub>r</sub>			—	—	—	
Output fall time		t <sub>f</sub>			—	—	—	
Common mode transient immunity at high level output		C <sub>MH</sub>	7	V <sub>CM</sub> = 600V, I <sub>F</sub> = 8mA, V <sub>CC</sub> = 30V, Ta = 25°C	-5000	—	—	V / μs
Common mode transient immunity at low level output		C <sub>ML</sub>	7	V <sub>CM</sub> = 600V, I <sub>F</sub> = 0mA, V <sub>CC</sub> = 30V, Ta = 25°C	5000	—	—	V / μs

\*All typical values are at Ta=25°C

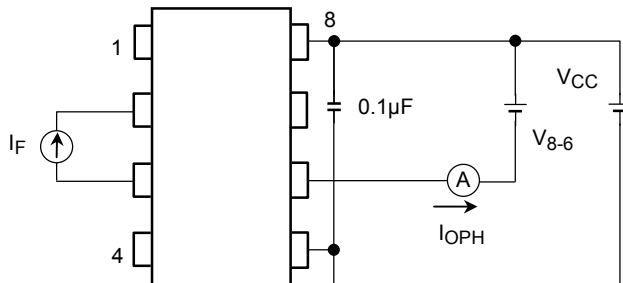
**Test Circuit 1:**



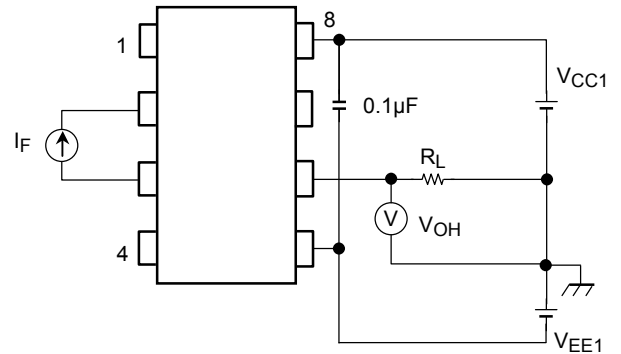
**Test Circuit 2:  $I_{OPL}$**



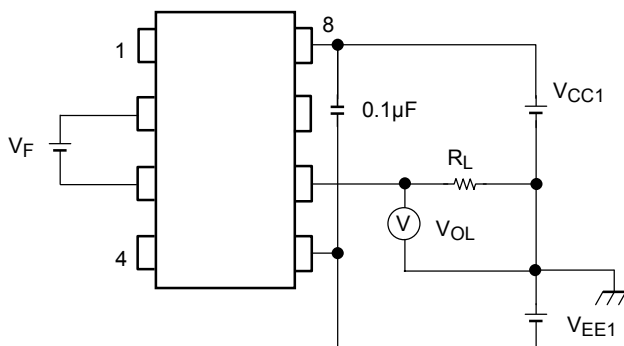
**Test Circuit 3:  $I_{OPH}$**



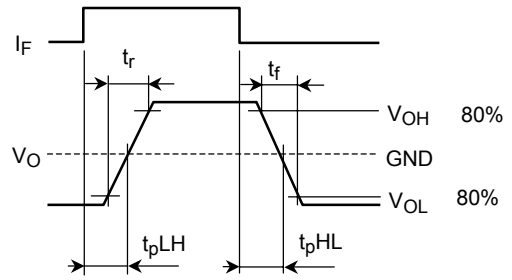
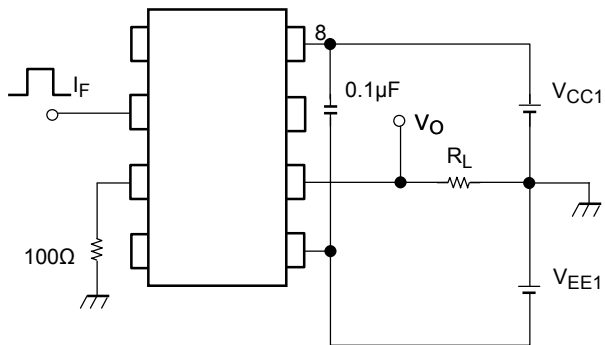
**Test Circuit 4:  $V_{OH}$**



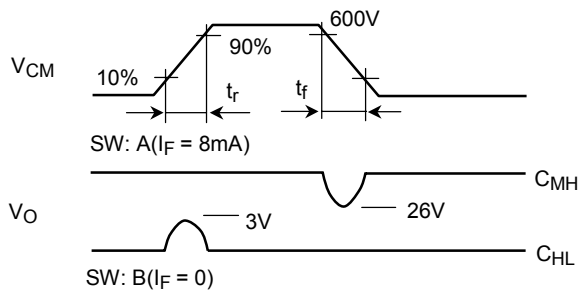
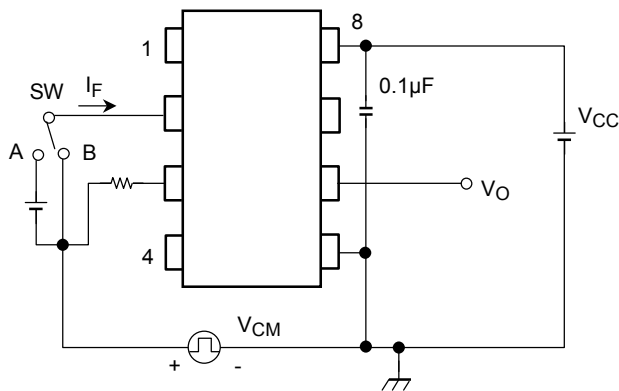
**Test Circuit 5:  $V_{OL}$**



**Test Circuit 6:  $t_{pLH}$ ,  $t_{pHL}$ ,  $t_r$ ,  $t_f$**



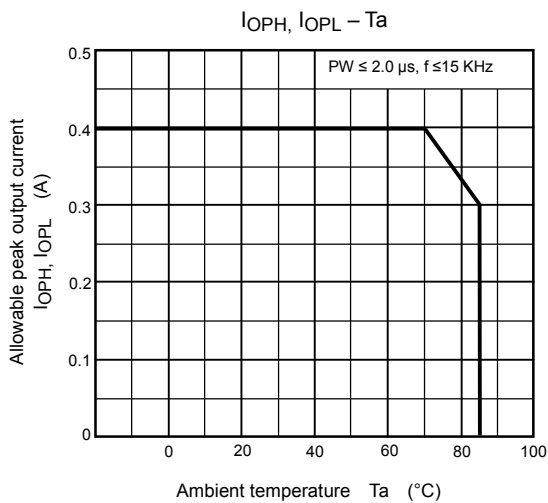
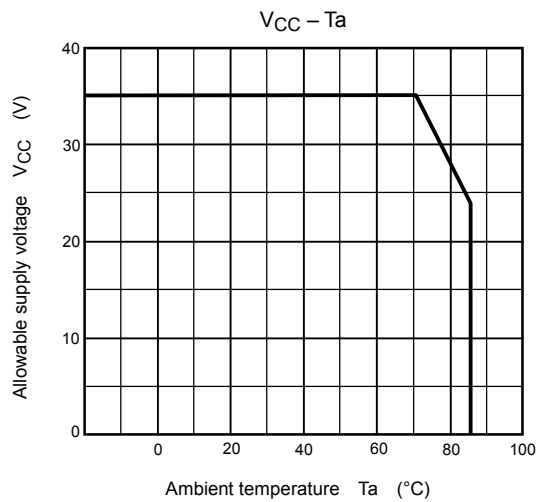
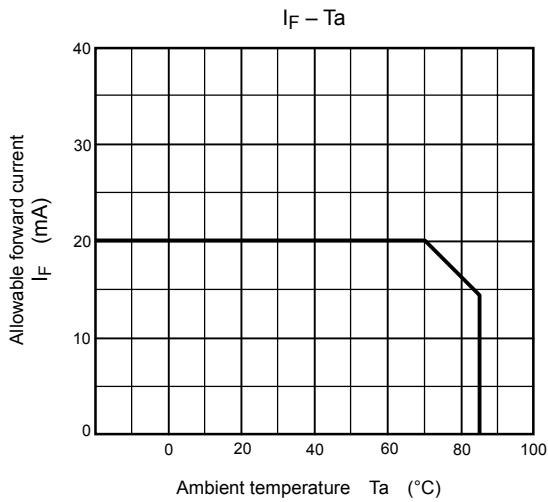
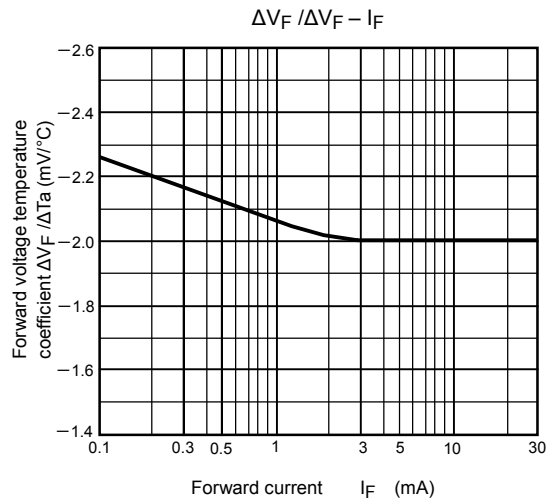
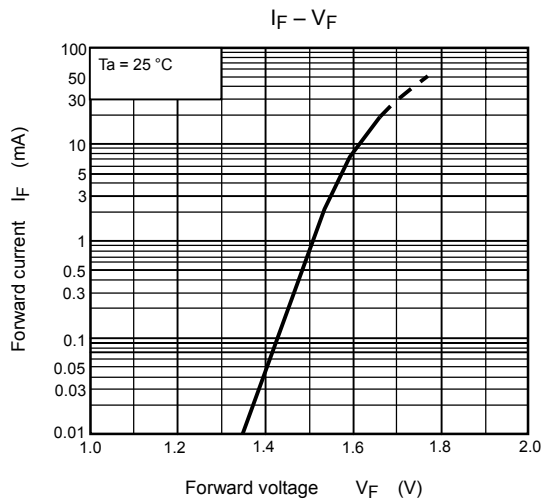
**Test Circuit 7:  $C_{MH}$ ,  $C_{ML}$**



$$C_{ML} = \frac{480(V)}{t_r(\mu s)}$$

$$C_{MH} = \frac{480(V)}{t_f(\mu s)}$$

$C_{ML}$  ( $C_{MH}$ ) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.



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